

Supporting Information

Sulfur Doping Enhanced Desorption of Intermediates on NiCoP for Efficient Alkaline Hydrogen Evolution

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Materials:

Sodium hypophosphite ($\text{NaH}_2\text{PO}_2 \cdot \text{H}_2\text{O}$), nickel nitrate hexahydrate ($\text{Ni}(\text{NO}_3)_2 \cdot 6\text{H}_2\text{O}$) and sulfur were purchased from Sinopharm Chemical Reagent Co., Ltd. (Shanghai, China). Cobalt nitrate hexahydrate ($\text{Co}(\text{NO}_3)_2 \cdot 6\text{H}_2\text{O}$) and urea ($\text{CO}(\text{NH}_2)_2$) were bought from Macklin Biochemical Co., Ltd. (Shanghai, China). CFP was purchased from He Sen Corporation (type: TGP-H-060). All the reagents were used as received.

Turnover Frequency Calculations.

The size of electrochemical active surface area (A_{ECSA}) can be calculated using the following formula^{1,2}:

$$A_{ECSA} = \frac{C_{dl-catalyst}(mF \cdot cm^{-2})}{C_{dl-CFP}(mF \cdot cm^{-2}) \text{ per } cm^2_{ECSA}} \quad (1)$$

The specific capacitance of CFP is normally treated as $0.04mF \cdot cm^{-2}$.

Turnover frequency (TOF) is calculated from the following formula:

$$TOF = \frac{\text{number of total } H_2 \text{ turnovers / geometric area}(cm^2)}{\text{number of surface active sites / geometric area}(cm^2)} \quad (2)$$

The number of total H_2 turnover can be calculated from the current density (j) according to:

$$\begin{aligned} \text{No. of } H_2 &= \left(|j| \frac{mA}{cm^2} \right) \left(\frac{1 Cs^{-1}}{1000mA} \right) \left(\frac{1 mol e^-}{96485.3 C} \right) \left(\frac{1 mol H_2}{2 mol e^-} \right) \left(\frac{6.022 \times 10^{23} H_2 \text{ molecules}}{1 mol H_2} \right) \\ &= 3.12 \times 10^{15} \frac{H_2 / s}{cm^2} \text{ per } \frac{mA}{cm^2} \end{aligned} \quad (3)$$

Since the nature of the surface active sites is not yet clarified and the exact hydrogen binding site is not known, we estimate the number of active sites as the total number of surface sites (including both Ni, Co, P and S atoms as possible active sites) from the unit cell of the catalysts, which may underestimate the real TOF.

The active sites per real surface area is calculated from the following formula:

$$\text{No. of active sites} = \left(\frac{\text{No. of atoms / unit cell}}{\text{Volume / unit cell}} \right)^{\frac{2}{3}} \quad (4)$$

We can calculate the number of active sites per real surface area for each phase. The exact cell parameters of $\text{Ni}_{1.5}\text{Co}_{1.5}\text{S}_4$ is from the average value of NiCo_2S_4 and CoNi_2S_4 .

$$\text{No. of active sites}(\text{NiCoP}) = \left(\frac{9 \text{ atoms / unit cell}}{98.77 \text{ \AA} / \text{unit cell}} \right)^{\frac{2}{3}} = 2.02 \times 10^{15} \text{ atoms cm}^2 \quad (5)$$

$$\text{No. of active sites}(\text{Ni}_{1.5}\text{Co}_{1.5}\text{S}_4) = \left(\frac{14 \text{ atoms / unit cell}}{825.56 \text{ \AA} / \text{unit cell}} \right)^{\frac{2}{3}} = 6.60 \times 10^{14} \text{ atoms cm}^2$$

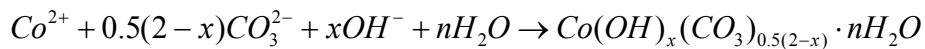
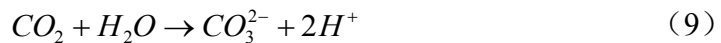
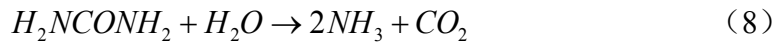
(6)

Finally, the TOF can be calculated from the following formula:

$$\text{TOF} = \frac{\left(3.12 \times 10^{15} \frac{\text{H}_2 / \text{s}}{\text{cm}^2} \text{ per } \frac{\text{mA}}{\text{cm}^2} \right) \times |j|}{\text{No. of active sites} \times A_{\text{ECSA}}} \quad (7)$$

The formation of precursor NWs.

The precursor is a template as a nanowire array. Its formation can be expressed by the following chemical reaction equation:



(10)

The doping of Ni replaces the position of Co in the unit cell without changing the phase.

The speed of crystal growth is controlled by the process conditions to grow along the surface with the highest energy to form single crystal nanowires, and a uniform ordered nano-array is formed on the surface of the carbon fiber.

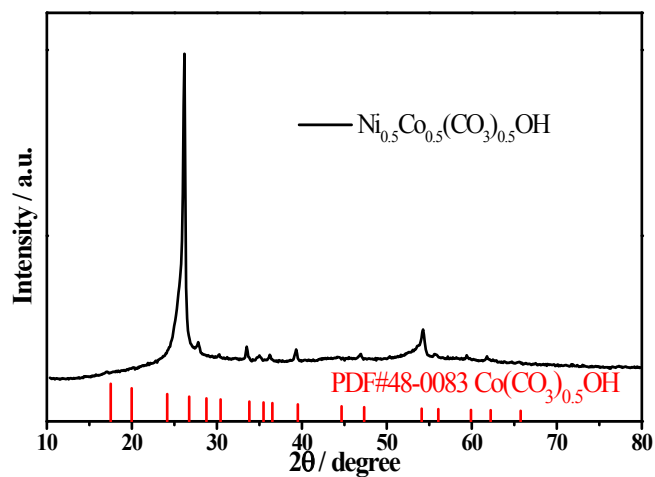


Figure S1. XRD of the precursor.

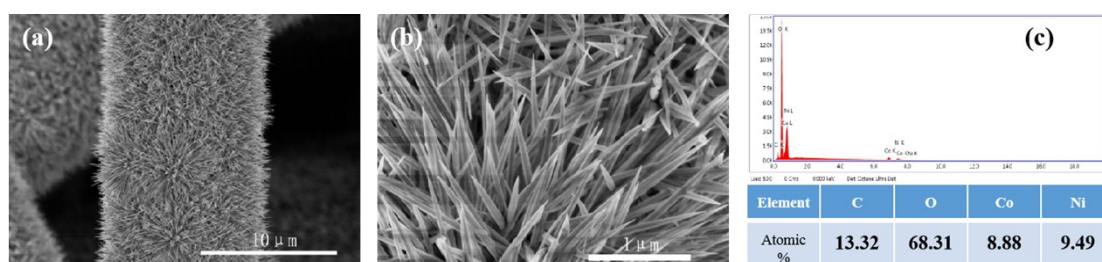


Figure S2. (a,b) SEM, (c) EDS of the precursor.

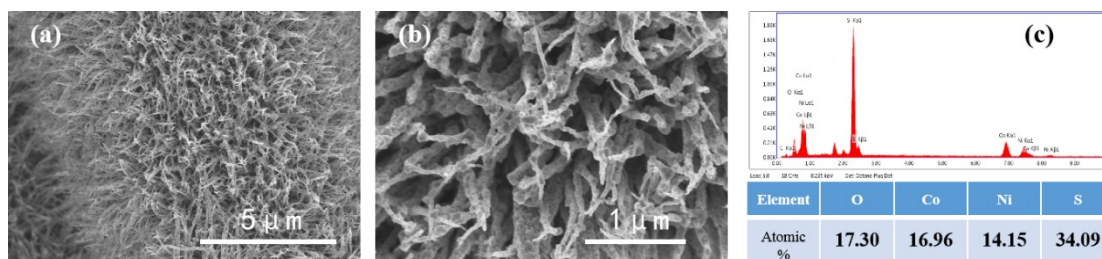


Figure S3. (a,b) SEM, (c) EDS of NiCo-sulfide NWs

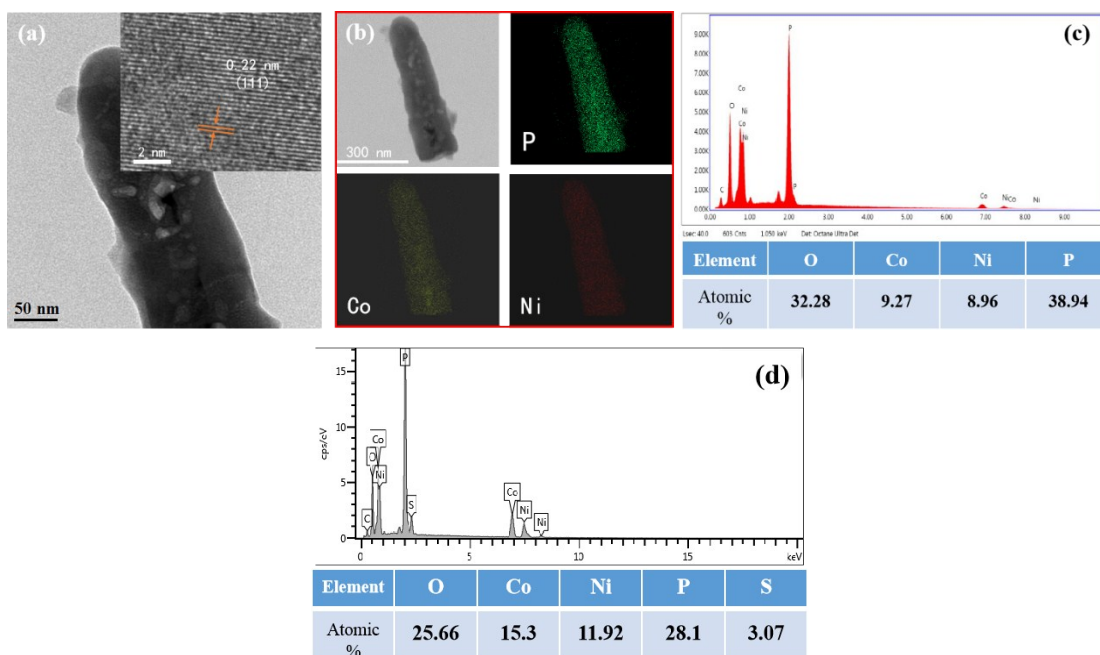


Figure S4. (a) TEM image, (b) EDS elemental mapping, (c) EDS of NiCoP NWs, (d) EDS of S-NiCoP NWs. Inset in (a): HRTEM image of NiCoP NWs.

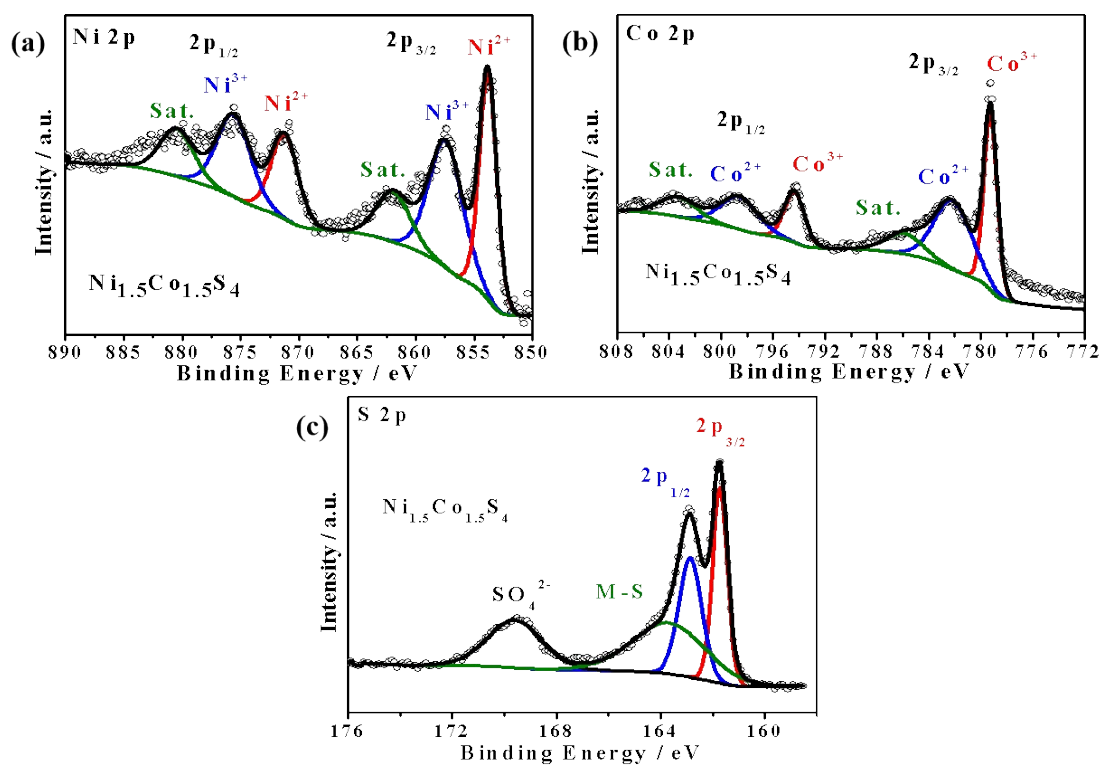


Figure S5. XPS of (a) Ni 2p, (b) Co 2p and (c) S 2p of $\text{Ni}_{1.5}\text{Co}_{1.5}\text{S}_4$.

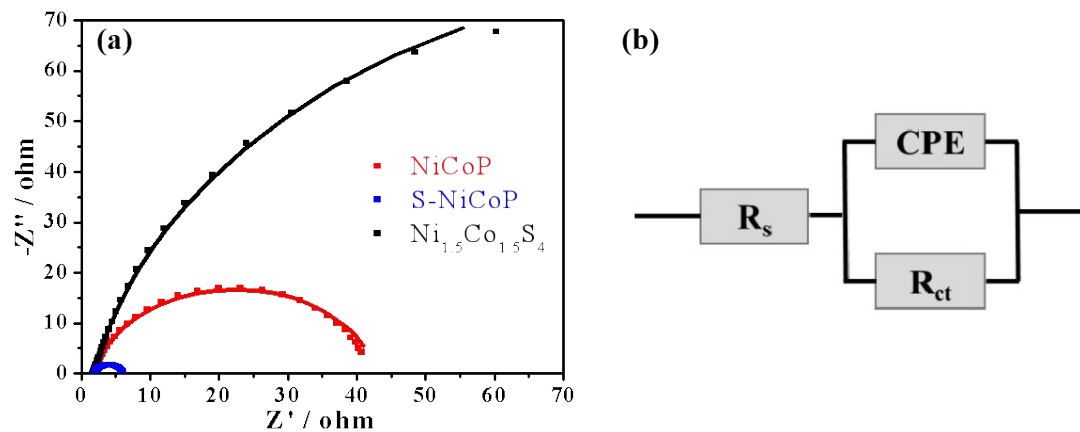


Figure S6. (a) EIS Nyquist plots and (b) The equivalent circuit.

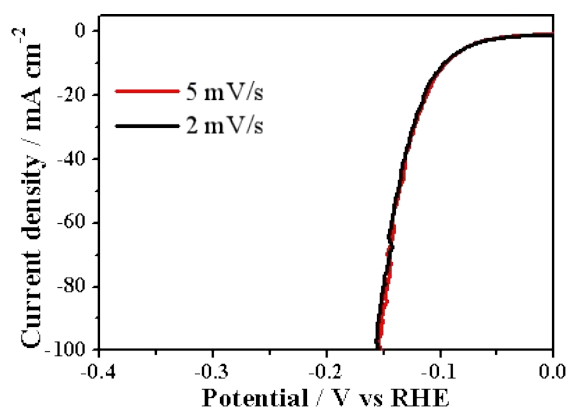


Figure S7. Linear sweeping voltammetry of S-NiCoP NWs at different scan rate. The HER performance of the sample is hardly affected by the scan rate.

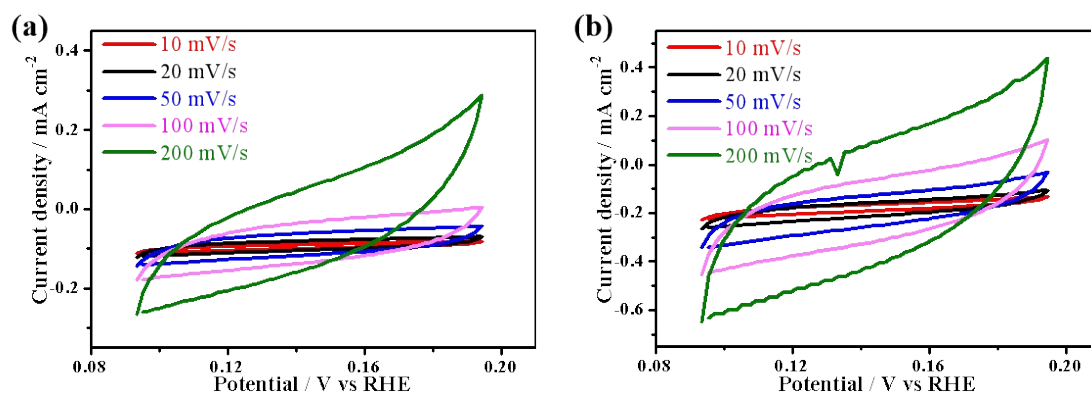


Figure S8. Electrochemical double-layer capacitance measurements of (a) NiCoP and (b) S-NiCoP.

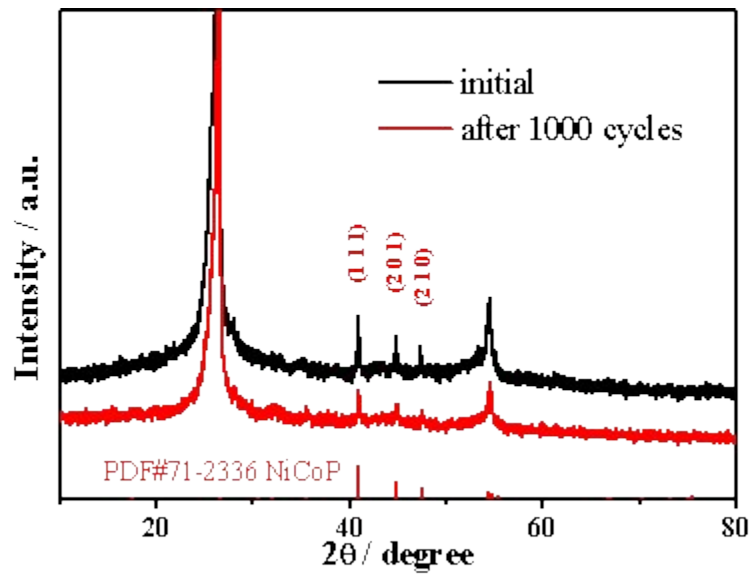


Figure S9. XRD of S-NiCoP NWs before and after 1000 cycles.

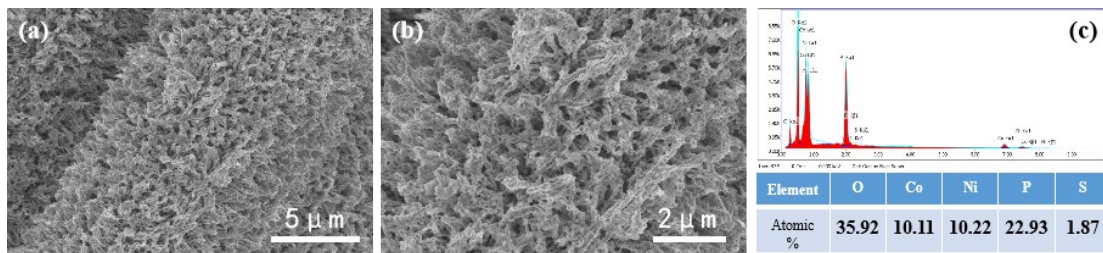


Figure S10. (a,b) SEM, (c) EDS of S-NiCoP NWs after 1000 cycles.

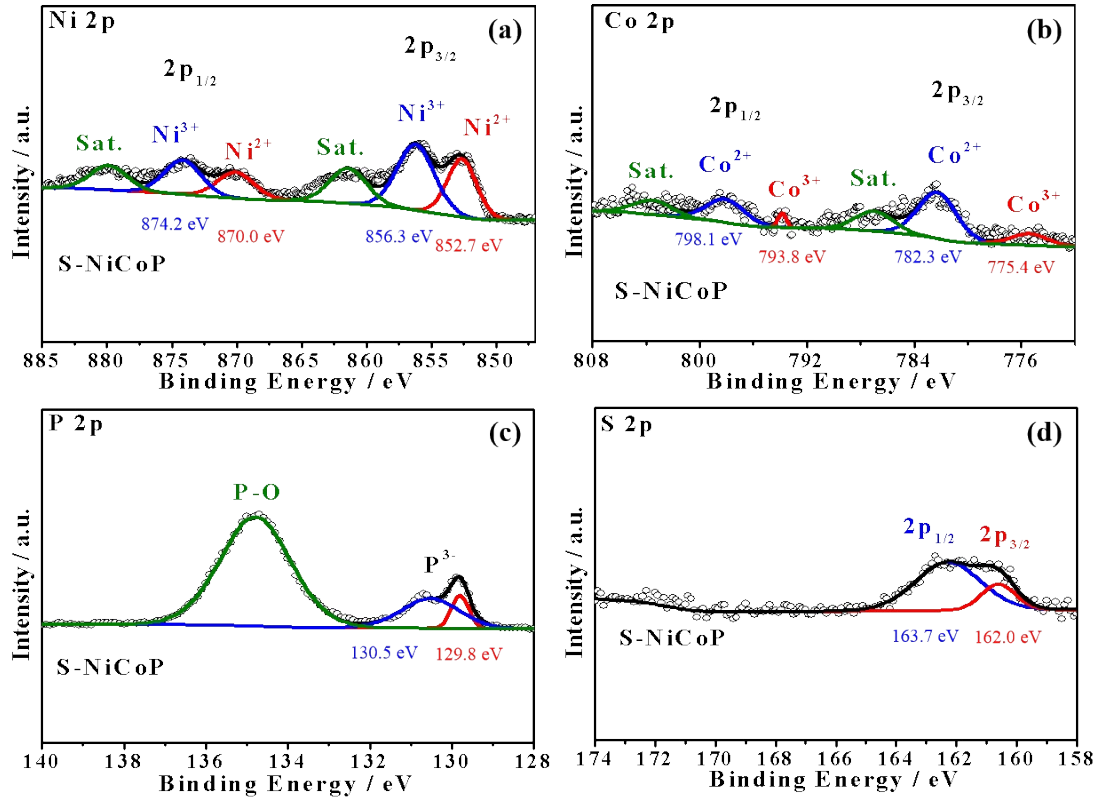


Figure S11. XPS of (a) Ni 2p, (b) Co 2p, (c) P 2p and (d) S 2p of S-NiCoP NWs after 1000 cycles.

As shown in Figures S12-S15, the content of S could be fine adjusted through reducing the content of P source and shortening the phosphorization time. The obtained samples were named according to the P/S ratio (from EDS in Figure S4, S12 and S13). If only a small amount of S atoms are doped (NiCo-P_{0.90}S_{0.10} and NiCo-P_{0.77}S_{0.23}), the samples will maintain the structure of nanowires (Figure 1e,f and Figure S12a) and the main phase of NiCoP (Figure 1b and Figure S14a). However, if a larger amount of S atoms are doped (NiCo-P_{0.45}S_{0.55}), micro-flakes appeared (Figure S13a) with new phases of CoPS and NiCo₂S₄ (Figure S14b).

As shown in Figure S15a, the η_{100} values of NiCo-P_{0.90}S_{0.10} and NiCo-P_{0.77}S_{0.23} are lowered from 260 mV of pure NiCo-P down to 172 mV and 245 mV, respectively, but that of NiCo-P_{0.45}S_{0.55} is increased up to 337 mV. It indicates that a small amount of S doping (NiCo-P_{0.90}S_{0.10} and NiCo-P_{0.77}S_{0.23}) could regulate the electronic states and improve the HER performances of NiCoP, although the morphology and phase are maintained. NiCo-P_{0.90}S_{0.10} exhibits the best HER performance. As for NiCo-P_{0.45}S_{0.55} with larger amount of S dopants, the HER activity is lowered due to the changed morphology and phase transition. The Tafel slope (Figure S15b) of NiCo-P_{0.90}S_{0.10} (63.3 mV·dec⁻¹) is also the smallest one, that is, an appropriate S doping could promote the electron transfer during the Heyrovsky reaction and increase the HER activity.

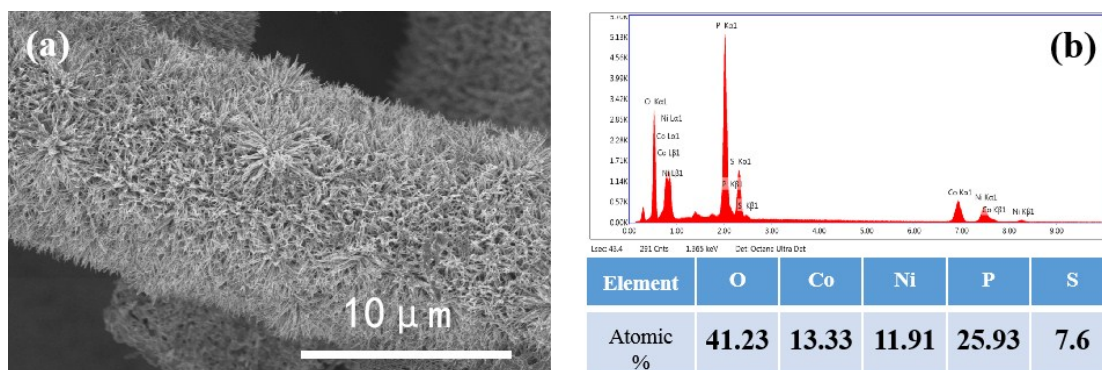


Figure S12. (a) SEM, (b) EDS of NiCo-P_{0.77}S_{0.23} NWs.

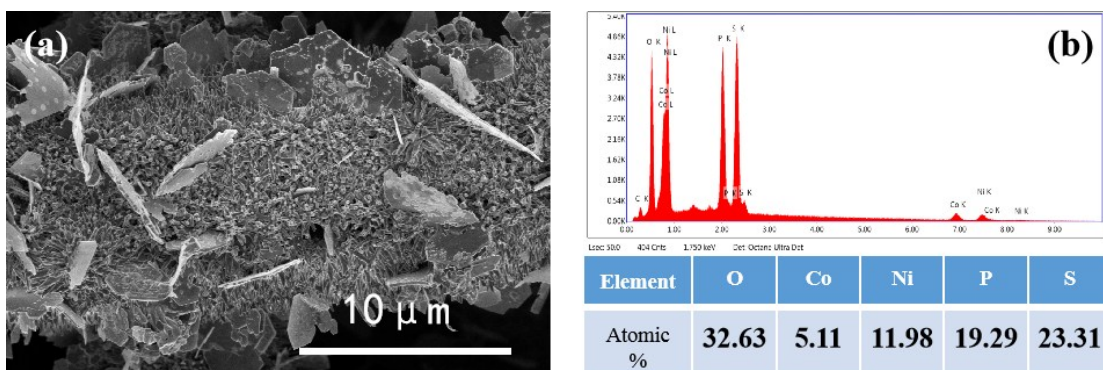


Figure S13. (a) SEM, (b) EDS of NiCo-P_{0.45}S_{0.55} NWs.

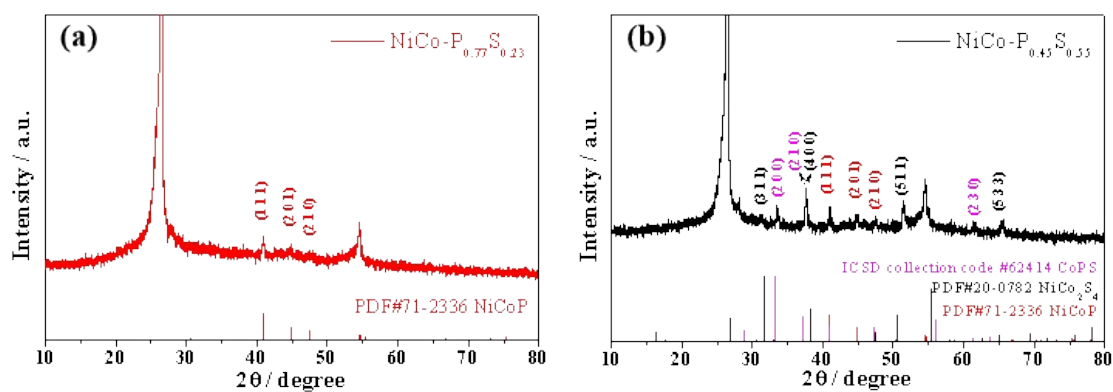


Figure S14. XRD of (a) NiCo-P_{0.77}S_{0.23} NWs and (b) NiCo-P_{0.45}S_{0.55} NWs. The phase CoPS is from literature³.

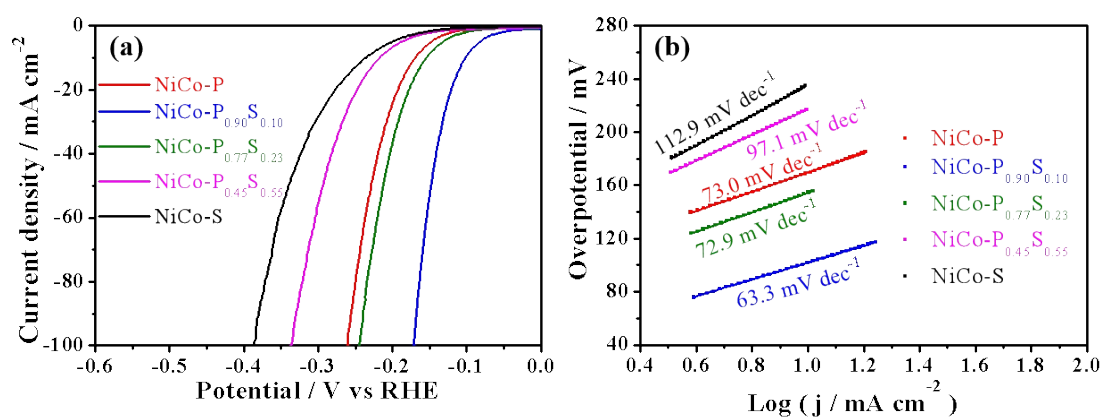


Figure S15. (a) Linear sweeping voltammetry, (b) Tafel plots for different content of sulfur. NiCo-P, NiCo-P_{0.90}S_{0.10} and NiCo-S denote NiCoP, S- NiCoP and Ni_{1.5}Co_{1.5}S₄ in this paper, respectively.

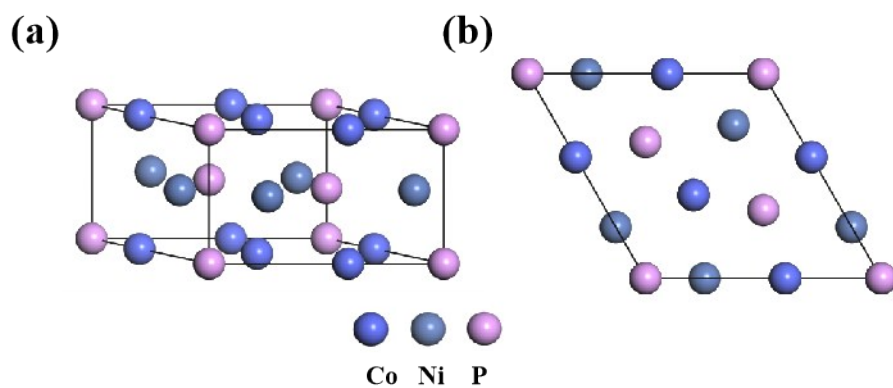


Figure S16. Bulk NiCoP: (a) side view and (b) top view.

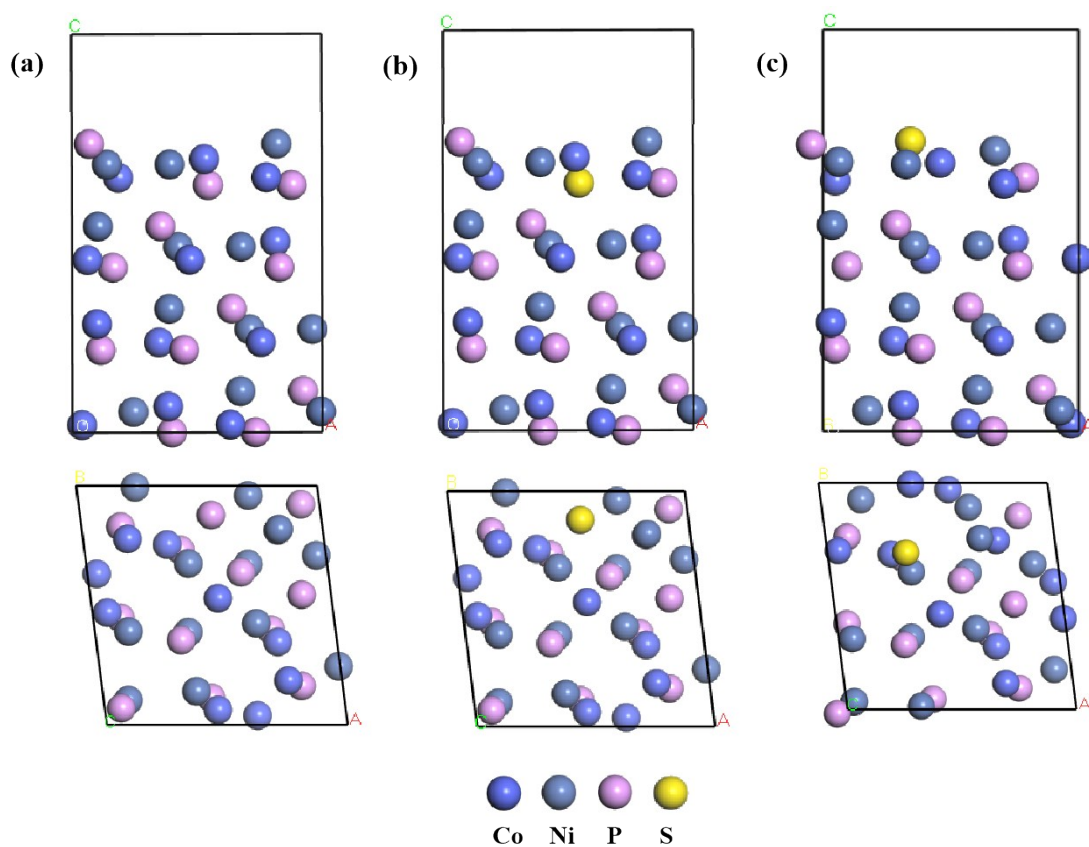


Figure S17. The (111) facet of (a) NiCoP, (b) S-NiCoP before structural optimization, (c) S-NiCoP after structural optimization.

Table S1. The binding energy with H₂O* or H* adsorbed on different sites of S-NiCoP

Adsorbate	H ₂ O*		H*	
	Ni	Co	Ni	Co
Binding energy / eV	-240.690561	-240.815172	-229.1303221	-229.7176027

The d band center (ϵ_d) in Figure 4e can be calculated from the following formula:

$$\epsilon_d = \frac{\int_{-\infty}^{\infty} x\rho(x)dx}{\int_{-\infty}^{\infty} \rho(x)dx}, \quad (11)$$

in which x and $\rho(x)$ denote the energy (eV) and d-pdos of Co in Figure 4e.

Table S2. Comparison of HER performance of S-NiCoP with other electrocatalysts.

Catalyst	η_{10} / mV	η_{100} / mV	Electrolyte	References
S-NiCoP NW/CFP	102	170	1M KOH	This work
Ni _{0.51} Co _{0.49} P	82		1M KOH	Adv. Funct. Mater., 2016, 26, 7644-7651
NiCoP nanocone arrays/NF	104		1M KOH	J. Mater. Chem. A., 2017, 5, 14828-14837
(Co _{0.52} Fe _{0.48}) ₂ P	79		1M KOH	Energy Environ. Sci, 2016, 9, 2257
Ni ₅ P ₄ nanocrystals	118		0.5M H ₂ SO ₄	J. Mater. Chem. A., 2015, 3, 1656
CoP/CC	67	204	0.5M H ₂ SO ₄	J. Am. Chem. Soc., 2014, 136, 7587
Ni ₂ P-NiCoP/NCCs	116		1.0 M NaOH	J. Mater. Chem. A., 2017, 32, 16568-16572
S-CoP/NF	109	185	1M KOH	Nano Energy, 2018, 53, 286-295
Ni-modified CoP NPs	180		1M KOH	J. Mater. Chem. A., 2016, 20, 7549-7554
CoP NPs	170		1M KOH	Nano Energy, 2016, 29, 37-45
CoP/RGO	200		1M KOH	Chem. Sci., 2016, 7, 1690-1695
O-NiCoP	44		1M KOH	Small, 2018, 14, 1613-6829
NiCo ₂ P _x /CF	58	127	1M KOH	Advanced Materials, 2017, 29,1605502
S-Ni ₅ P ₄ NPA/CP	56	104	0.5M H ₂ SO ₄	ACS Appl Mater Interfaces, 2018, 10, 26303-26311
Ni ₂ P-Co ₂ P/NC	251		1M KOH	Inter. J. Hydrogen Energy, 2019, 44, 14908-14917
V-CoP/CC	71		1M KOH	Chem. Sci., 2018, 9, 1970-1975
	123		1M PBS	
	47		0.5M H ₂ SO ₄	
NiCoP-C(TPA)/NF	78	~175	1M KOH	Catalysis Science & Technology, 2019, 9, 4651-4658.
	94		0.5M H ₂ SO ₄	
	248		1M PBS	

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3. M. Caban-Acevedo, M. L. Stone, J. R. Schmidt, J. G. Thomas, Q. Ding, H. C. Chang, M. L. Tsai, J. H. He and S. Jin, *Nature materials*, 2015, **14**, 1245-1251.